MOSFETs Silicon N-Channel MOS (π-MOSⅦ)

TK2A65D

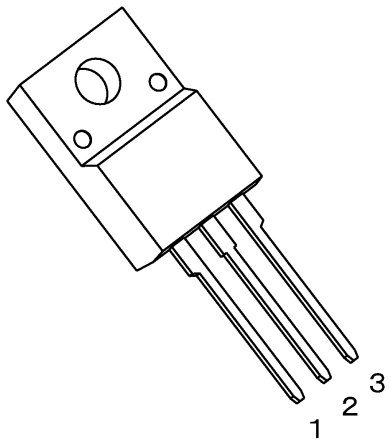
1. Applications

- Switching Voltage Regulators

2. Features

(1) Low drain-source on-resistance: $R_{DS(ON)}$ = 2.8 Ω (typ.)
(2) High forward transfer admittance: $|Y_{fs}|$ = 1.5 S (typ.)
(3) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 650 V)
(4) Enhancement mode: V_{th} = 2.4 to 4.4 V (V_{DS} = 10 V, I_D = 1 mA)

3. Packaging and Internal Circuit



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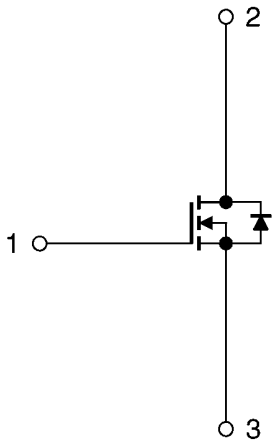


1: Gate (G)
2: Drain (D)
3: Source (S)

4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	650	V
Gate-source voltage		V_{GSS}	±30	
Drain current (DC)	(Note 1)	I_D	2	A
Drain current (pulsed)	(Note 1)	I_{DP}	8	
Power dissipation	(T_c = 25°C)	P_D	30	W
Single-pulse avalanche energy	(Note 2)	E_{AS}	195	mJ
Avalanche current		I_{AR}	2	A
Repetitive avalanche energy	(Note 3)	E_{AR}	3.0	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

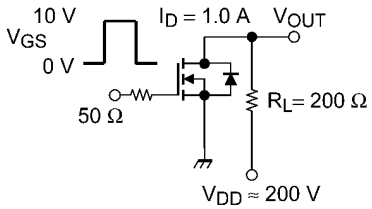
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	—	—	±1	μA
Drain cut-off current	I_{DSS}	V_{DS} = 650 V, V_{GS} = 0 V	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = 10 mA, V_{GS} = 0 V	650	—	—	V
Gate threshold voltage	V_{th}	V_{DS} = 10 V, I_D = 1 mA	2.4	—	4.4	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 1.0 A	—	2.8	3.26	Ω
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 1.0 A	0.4	1.5	—	S

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	—	380	—	pF
Reverse transfer capacitance	C_{rss}		—	2.5	—	
Output capacitance	C_{oss}		—	45	—	
Switching time (rise time)	t_r	See Figure 6.2.1.	—	15	—	ns
Switching time (turn-on time)	t_{on}		—	35	—	
Switching time (fall time)	t_f		—	7	—	
Switching time (turn-off time)	t_{off}		—	55	—	



Duty ≤ 1%, t_w = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ 400 V, V_{GS} = 10 V, I_D = 2 A	—	9	—	nC
Gate-source charge	Q_{gs}		—	5	—	
Gate-drain charge	Q_{gd}		—	4	—	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 1)	I_{DR}	—	—	—	2	A
Reverse drain current (pulsed) (Note 1)	I_{DRP}	—	—	—	8	
Diode forward voltage	V_{DSF}	I_{DR1} = 2 A, V_{GS} = 0 V	—	—	-1.7	V
Reverse recovery time	t_{rr}	I_{DR} = 2 A, V_{GS} = 0 V $-dI_{DR}/dt$ = 100 A/μs	—	700	—	ns
Reverse recovery charge	Q_{rr}		—	3.5	—	μC

8. Characteristics Curves (Note)

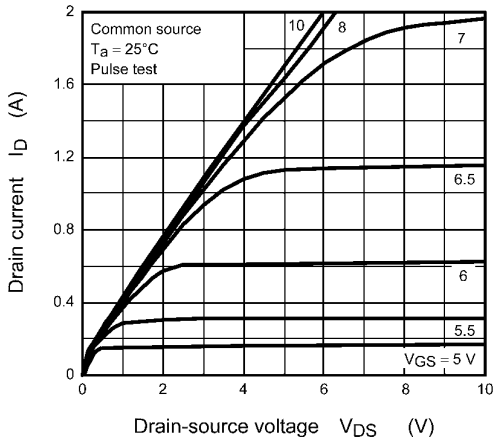


Fig. 8.1 I_D - V_{DS}

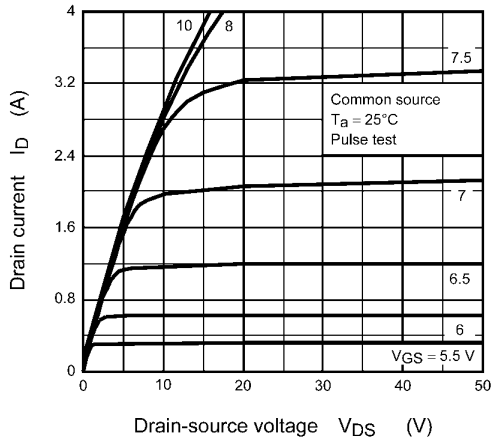


Fig. 8.2 I_D - V_{DS}

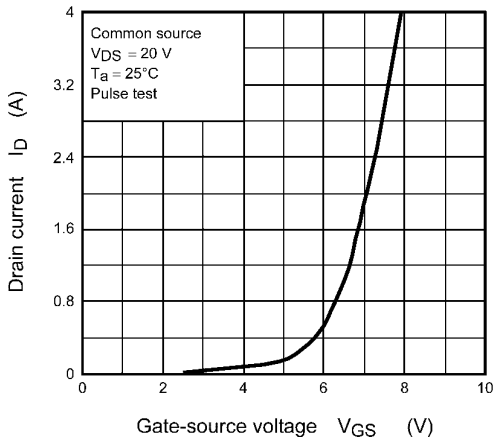


Fig. 8.3 I_D - V_{GS}

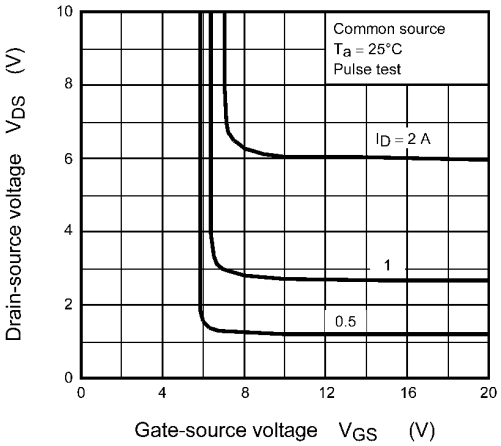


Fig. 8.4 V_{DS} - V_{GS}

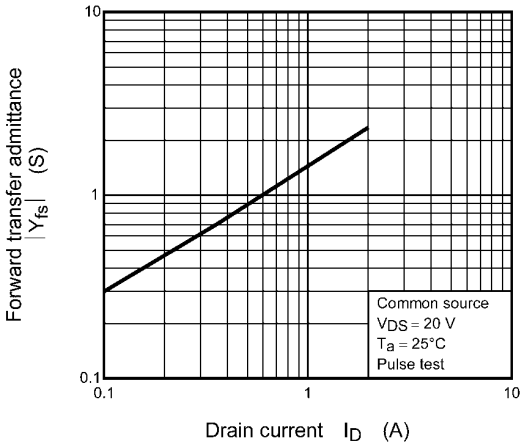


Fig. 8.5 $|Y_{fs}|$ - I_D

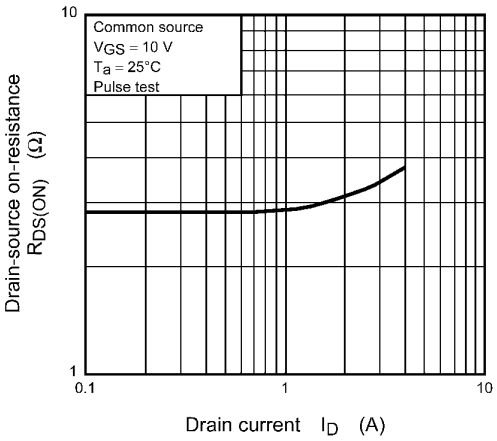


Fig. 8.6 $R_{DS(ON)}$ - I_D